Amendments to the Claims:

1. (Currently Amended) A method of making fused silica, comprising: generating a plasma;

delivering reactants comprising a silica precursor into the plasma to produce silica particles; and

depositing the silica particles on a <u>rotating horizontal</u> deposition surface <u>while at the same time consolidating the particles</u> to form glass.

- 2. (Original) The method of claim 1, wherein delivering reactants comprising a silica precursor into the flame further comprises delivering a dopant material into the plasma to form doped silica particles.
- 3. (Original) The method of claim 2, wherein the dopant material comprises a compound capable of being converted to an oxide of at least one member of the group consisting of B, Al, Ge, K, Ca, Sn, Ti, P, Se, Er, and S.
- 4. (Original) The method of claim 2, wherein the dopant material comprises a fluorine compound.
- 5. (*Original*) The method of claim 4, wherein the fluorine compound is selected from the group consisting of CF₄, CF_xCl_{4-x}, where x ranges from 1 to 3, NF₃, SF₆, SiF₄, C₂F₆, and F₂.
- 6. (Original) The method of claim 1, wherein the plasma is generated by induction with a high frequency generator.
- 7. (Original) The method of claim 1, wherein the silica precursor is substantially free of hydrogen.
 - 8. (Original) The method of claim 7, wherein the silica precursor comprises SiCl₄.

- 9. (Original) The method of claim 1, wherein the glass is formed in an enclosure having a water vapor content less than 1 ppm by volume.
 - 10. (Canceled)
- 11. (Currently Amended) The method of elaim 10, claim 4, wherein the silica precursor and fluorine compound are delivered into the plasma in gaseous form.
- 12. (Currently Amended) The method of elaim 10, claim 4, wherein the silica precursor is substantially free of hydrogen.
 - 13. (Original) The method of claim 12, wherein the silica precursor comprises SiCl₄.
- 14. (*Currently Amended*) The method of claim 10, claim 4, wherein the fluorine compound is selected from the group consisting of CF₄, CF_xCl_{4-x}, where x ranges from 1 to 3, NF₃, SF₆, SiF₄, C₂F₆, and F₂.
- 15. (Currently Amended) The method of claim 10, claim 4, wherein the glass is formed in an enclosure having a water vapor content less than 1 ppm by volume.
 - 16-23. (Canceled)